# SK 40GB123



# SEMITOP® 2

## **IGBT** Module

## SK 40GB123

**Preliminary Data** 

## **Features**

- Compact design
- · One screw mounting
- · Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- · N-channel homogeneous silicon structure (NPT-Non punch-through IGBT)
- · Low tail current with low temperature dependence

## Typical Applications\*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

## Remarks

• V<sub>F</sub> = chip level value

Absolute Maximum Ratings T <sub>s</sub> = 25 °C, unless otherwise specific					
Symbol	Conditions		Values	Units	
IGBT	•				
$V_{CES}$	T <sub>j</sub> = 25 °C		1200	V	
I <sub>C</sub>	T <sub>j</sub> = 125 °C	T <sub>s</sub> = 25 °C	40	Α	
		T <sub>s</sub> = 80 °C	27	Α	
I <sub>CRM</sub>	I <sub>CRM</sub> = 2 x I <sub>Cnom</sub>		60	Α	
$V_{GES}$			± 20	٧	
t <sub>psc</sub>	$V_{CC}$ = 600 V; $V_{GE} \le 20$ V; $V_{CES} < 1200$ V	T <sub>j</sub> = 125 °C	10	μs	
Inverse D	Piode				
I <sub>F</sub>	T <sub>j</sub> = 150 °C	$T_s = 25 ^{\circ}C$	48	Α	
		$T_s = 80  ^{\circ}C$	34	Α	
I <sub>FRM</sub>	I <sub>FRM</sub> = 2 x I <sub>Fnom</sub>		60	Α	
Module					
I <sub>t(RMS)</sub>				Α	
$T_{vj}$			-40 <b>+</b> 150	°C	
T <sub>stg</sub>			-40 <b>+</b> 125	°C	
V <sub>isol</sub>	AC, 1 min.		2500	V	

Characteristics $T_s =$			25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						•
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_{C} = 1.2 \text{ mA}$		4,5	5,5	6,5	V
I <sub>CES</sub>	V <sub>GE</sub> = 30 V, V <sub>CE</sub> = V <sub>CES</sub>	T <sub>j</sub> = 25 °C			0,2	mA
		T <sub>j</sub> = 125 °C				mA
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 30 V	T <sub>j</sub> = 25 °C			560	nA
		T <sub>j</sub> = 125 °C				nA
V <sub>CE0</sub>		T <sub>j</sub> = 25 °C		1,2		V
		T <sub>j</sub> = 125 °C		1,2		V
r <sub>CE</sub>	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		43		mΩ
		T <sub>j</sub> = 125°C		63		$m\Omega$
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 30 A, V <sub>GE</sub> = 15 V		2	2,5	3	V
		T <sub>j</sub> = 125°C <sub>chiplev.</sub>		3,1	3,7	V
C <sub>ies</sub>				2		nF
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz		0,3		nF
C <sub>res</sub>				0,14		nF
t <sub>d(on)</sub>				35		ns
Į ζ,	$R_{Gon} = 20 \Omega$	V <sub>CC</sub> = 600V		45		ns
Ė <sub>on</sub>	D 00 0	I <sub>C</sub> = 30A		3,2		mJ
<sup>L</sup> d(off)	$R_{Goff} = 20 \Omega$	T <sub>j</sub> = 125 °C		250		ns
t <sub>f</sub>		V <sub>GE</sub> =±15V		45		ns
E <sub>off</sub>				3,6		mJ
$R_{\text{th(j-s)}}$	per IGBT				0,85	K/W



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## **Features**

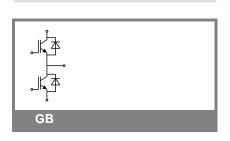
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Characteristics							
Symbol	Conditions		min.	typ.	max.	Units	
Inverse Diode							
$V_F = V_{EC}$	$I_{Fnom}$ = 30 A; $V_{GE}$ = 0 V	T <sub>j</sub> = 25 °C <sub>chiplev.</sub>		2		V	
		$T_j = 125  ^{\circ}C_{chiplev.}$		1,8		V	
$V_{F0}$		T <sub>j</sub> = 125 °C		1	1,2	٧	
r <sub>F</sub>		T <sub>j</sub> = 125 °C		53	73	mΩ	
I <sub>RRM</sub>	I <sub>F</sub> = 30 A	T <sub>j</sub> = 125 °C		32		Α	
$Q_{rr}$	di/dt = 400 A/µs			5,4		μC	
E <sub>rr</sub>	V <sub>CC</sub> = 600V			1,2		mJ	
$R_{th(j-s)D}$	per diode				1	K/W	
$M_s$	to heat sink M1				2	Nm	
w			_	21		g	

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

